Preliminary Data Sheet





SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to meet our customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.



Triple Junction TO-9

High Power Single-Mode and Multi-Mode SemiNex Lasers

- 12xx to 19xx nm Custom Wavelengths Available Lensed Options Available

ApplicationsOEM Medical

- Professional Medical Lidar .
 - Military / Aerospace
- Illumination

- FeaturesCost effective

- Cost effective
 High Output Power
 High Dynamic Range
 High Efficiency
 Standard Low Cost Package



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PI Sheet

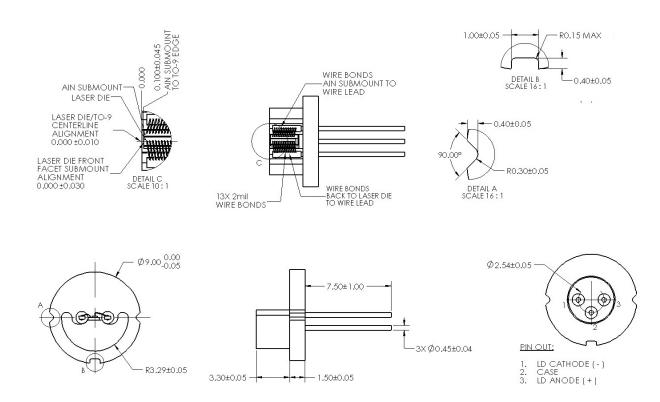






	Symbol	TO9-264	Units
Optical			
Wavelength	λ _c	1550	nm (±20)
Output Power (<10ns)	P°	25.00	watts (±10%)
Output Power (150ns)	P	15.00	watts (±10%)
Chip Cavity Length	CL	2500	μm
No. of Junctions		3	
Emitter Width	W	50	μm
Emitter Height	Н	10	μm
Spectral Width	δλ	22	nm 3dB
Slope Efficiency	η°	0.80	W/A
Fast Axis Div.*	O_perp	28	deg FWHM
Slow Axis Div.	O_parallel	12	deg FWHM
Electrical			
Power Conversion Eff.	η	8	%
Operating Current (<10ns)	I _{op}	40	A
Operating Current (150ns)	I _{op}	20	A
Threshold Current	I _{th}	0.4	А
Operating Voltage	V _{op}	9	V
Mechanical			
Weight		0	g
Operating Temp.**		-40 to 85	°C
Storage Temp.		-40 to 85	°C

Specified values are rated at a constant heat sink temperature of 20°C.
**Specified operating conditions are based on 20C heat sink temperature. High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.
Uncapped TO9 specifications assume heatsinking underneath laser chip.
Capped TO9 specifications assume heatsinking only on flat surface where pins extend.



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